POWER·MOS FET
FIELD EFFECT POWER TRANSISTOR

2N6660,1

1.2 AMPERES
60, 90 VOLTS
$R_{DS(ON)}$ = 3.0 Ω

This series of N-Channel Enhancement-mode Power MOSFETs utilizes GE's advanced Power DMOS technology to achieve low on-resistance with excellent device ruggedness and reliability.

This design has been optimized to give superior performance in most switching applications including: switching power supplies, inverters, converters and solenoid/relay drivers. Also, the extended safe operating area with good linear transfer characteristics makes it well suited for many linear applications such as audio amplifiers and servo motors.

Applications

- Switching power supplies
- DC to DC inverters
- CMOS and TTL to high current interface
- Line drivers
- Logic buffers
- Pulse amplifiers
- High frequency linear amplifiers

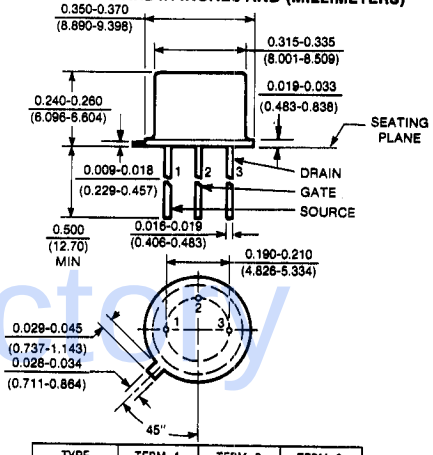
Features

- High speed, high current switching
- Current sharing capability when paralleled
- Directly interface to CMOS, DTL, TTL logic
- Simple DC biasing
- Extended safe operating area
- Inherently temperature stable
- Typical t_{on} and t_{off} < 5ns

Datasheet.Directory

N-CHANNEL

CASE STYLE TO-205AD (TO-39)
DIMENSIONS ARE IN INCHES AND (MILLIMETERS)



TYPE	TERM. 1	TERM. 2	TERM. 3
TO-205AD	SOURCE	GATE	DRAIN

maximum ratings (T_A = 25°C) (unless otherwise specified)

RATING	SYMBOL	2N6660	2N6661	UNITS
Drain-Source Voltage	V_{DSS}	60	90	Volts
Drain-Gate Voltage, R_{GS} = 1MΩ	V_{DGR}	60	90	Volts
Continuous Drain Current @ T_A = 25°C	I_D	1.2	1.2	A
Peak Drain Current(1)	I_{DM}	3.0	3.0	A
Gate-Source Voltage	V_{GS}	±30	±30	Volts
Total Power Dissipation @ T_A = 25°C Derate Above 25°C	P_D	6.25 50	6.25 50	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	°C

thermal characteristics

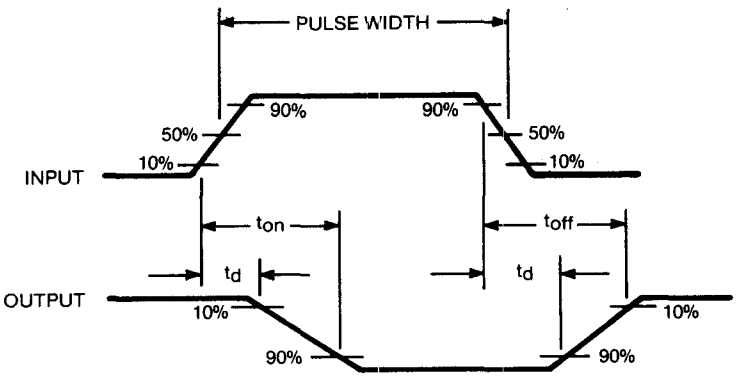
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	20°C	20×C	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/16" from Case for 10 Seconds	T_L	300	300	°C

(1) Repetitive Rating: Pulse width limited by max. junction temperature.

electrical characteristics (T_A = 25°C) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
off characteristics						
Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 10 μA)	2N6660	BV_{DSS}	90	—	—	Volts
	2N6661		60	—	—	
(V_{GS} = 0V, I_D = 2.5 MA)	2N6660		90	—	—	
	2N6661		60	—	—	
Zero Gate Voltage Drain Current (V_{DS} = Max Rating, V_{GS} = 0V)		I_{DSS}	—	—	10	μA
(V_{DS} = Max Rating, × 0.8, V_{GS} = 0V, T_A = 125°C)			—	—	500	
Gate-Source Leakage Current (V_{GS} = 15V, V_{DS} = 0V)		I_{GSS}	—	—	100	nA
(V_{GS} = 15V, V_{DS} = 0V - T_A = 125 °C)			—	—	500	
on characteristics*						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1 mA)		$V_{GS(TH)}$	0.8	—	2.0	Volts
Drain-Source Saturation Voltage (V_{GS} = 5V, I_D = 0.3A)	2N6660	$V_{DS(ON)}$	—	—	1.5	Volts
	2N6661		—	—	1.6	
Drain-Source Saturation Voltage (V_{GS} = 10V, I_D = 1.0A)	2N6660	$V_{DS(ON)}$	—	—	3.0	Volts
	2N6661		—	—	4.0	
On-State Drain Current (V_{DS} = 25V, V_{GS} = 10V)		$I_{D(ON)}$	1.0	—	—	Amp
Forward Transconductance (V_{DS} = 24V, I_D = 0.5A)		g_{fs}	.17	.25	—	mhos
dynamic characteristics						
Input Capacitance	V_{GS} = 0V, V_{DS} = 25V	C_{iss}	—	—	50	pF
Output Capacitance	f = 1 MHz	C_{oss}	—	—	40	pF
Reverse Transfer Capacitance	V_{DS} = 0V, V_{GS} = 0V	C_{rss}	—	—	10	pF
	f = 1.0 MHz	C_{rss}	—	—	35	pF
switching characteristics*						
Turn-on Delay Time	See switching times	$t_{d(on)}$	—	2	5	ns
Rise Time	waveform below	t_r	—	2	5	ns
Turn-off Delay Time		$t_{d(off)}$	—	2	5	ns
Fall Time		t_f	—	2	5	ns

*Pulse Test: Pulse width ≤ 300 μs, duty cycle ≤ 2%



SWITCHING TIME TEST WAVEFORMS